SN74ABT125Q-Q1 QUADRUPLE BUS BUFFER GATE WITH 3-STATE OUTPU

SCAS686B - DECEMBER 2002 - REVISED JANUARY 2008

14 🛛 V_{CC}

13 40E

12 4A

11 🛛 4Y

10 30E

9 🛛 3A

8 🛛 3Y

D PACKAGE (TOP VIEW)

1OE

1A 🛛 2

1Y 🛛 3

2A || 5 2Y 🛛 6

7

20E 14

GND [

- **Qualified for Automotive Applications**
- Typical V_{OLP} (Output Ground Bounce) <1 V at V_{CC} = 5 V, T_A = 25°C
- **High-Drive Outputs** (-16-mA I_{OH}, 32-mA I_{OL})
- Ioff and Power-Up 3-State Support Hot Insertion
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- ESD Protection Exceeds JESD 22 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)

description/ordering information

The SN74ABT125Q-Q1 quadruple bus buffer gate features independent line drivers with 3-state outputs. Each output is disabled when the associated output-enable (\overline{OE}) input is high.

This device is fully specified for hot-insertion applications using Ioff and power-up 3-state. The Ioff circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict.

To ensure the high-impedance state during power up or power down, OE should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

T _A	PACI	KAGE‡	ORDERABLE PART NUMBER	TOP-SIDE MARKING	
–40°C to 125°C	SOIC – D	Tape and reel	SN74ABT125QDRQ1	ABT125Q	

ORDERING INFORMATION[†]

⁺ For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

> FUNCTION TABLE - I- I- - - **6** - --

[‡] Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

_	(each buffer)									
ĺ	INP	JTS	OUTPUT							
ĺ	ŌĒ	Α	Y							
ſ	L	Н	Н							
	L	L	L							
	Н	Х	Z							



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

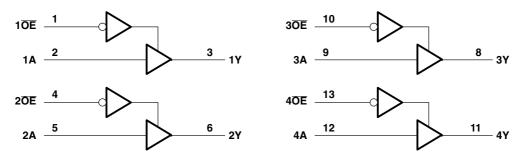


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logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage range, V_{CC} Input voltage range, V_I (see Note 1) Voltage range applied to any output in the high or power-off state, V_O Current into any output in the low state, I_O Input clamp current, I_{IK} ($V_I < 0$) Output clamp current, I_{OK} ($V_O < 0$)	0.5 V to 7 V -0.5 V to 5.5 V 126 mA 18 mA 50 mA
Package thermal impedance, θ_{JA} (see Note 2)	
Storage temperature range, T _{stg}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

2. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions (see Note 3)

		MIN	MAX	UNIT
V _{CC}	Supply voltage	4.5	5.5	V
V _{IH}	High-level input voltage	2		V
V _{IL}	Low-level input voltage		0.8	V
VI	Input voltage	0	V_{CC}	V
I _{OH}	High-level output current		-16	mA
I _{OL}	Low-level output current		32	mA
Δt/Δv	Input transition rise or fall rate		10	ns/V
$\Delta t / \Delta V_{CC}$	Power-up ramp rate	200		μs/V
T _A	Operating free-air temperature	-40	125	°C

NOTE 3: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.



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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER			7	Γ _A = 25°C					
PARA	MEIER	TEST CON	MIN	TYP [†]	MAX	MIN	MAX	UNIT	
V _{IK}		V _{CC} = 4.5 V,	l _l = –18 mA			-1.2		-1.2	V
		V _{CC} = 4.5 V,	I _{OH} = –3 mA	2.5			2.5		
V _{OH}		V _{CC} = 5 V,	I _{OH} = –3 mA	3			3		V
		$V_{CC} = 4.5 V$	I _{OH} = -16 mA	2			2		
V _{OL}		V _{CC} = 4.5 V	I _{OL} = 32 mA			0.55		0.55	V
V _{hys}					100				mV
l _l		$V_{CC} = 0$ to 5.5 V,	$V_I = V_{CC}$ or GND			±1		±1	μA
I _{OZPU}		V_{CC} = 0 to 2.1 V, V_{O} = 0.5 V to 2			±50		±50	μA	
I _{OZPD}		$V_{CC} = 2.1 \text{ V to } 0, V_{O} = 0.5 \text{ V to } 2.7 \text{ V}, \overline{OE} = X \pm 50$							μA
I _{OZH}		$V_{CC} = 2.1 V$ to 5.5 V,	$V_{O} = 2.7 \text{ V}, \ \overline{OE} \ge 2 \text{ V}$	10				10	μA
I _{OZL}		$V_{CC} = 2.1 V$ to 5.5 V,	$V_O = 0.5 \text{ V}, \ \overline{OE} \ge 2 \text{ V}$			-10		-10	μA
I _{off}		$V_{CC} = 0,$	$V_{I} \text{ or } V_{O} \leq 4.5 \text{ V}$			±100			μA
I _{CEX}		$V_{CC} = 5.5 V,$ $V_{O} = 5.5 V$	Outputs high			50		50	μA
lo‡		V _{CC} = 5.5 V,	V _O = 2.5 V	-50	-100	-200§	-50	-200§	mA
		V _{CC} = 5.5 V,	Outputs high		1	250		250	μA
Icc		$I_{O} = 0,$	Outputs low		24	30		30	mA
		$V_I = V_{CC}$ or GND	Outputs disabled		0.5	250		250	μA
	Data	$V_{CC} = 5.5 V$, One input at 3.4 V,	Outputs enabled			1.5		1.5	
∆l _{CC} ¶	inputs	Other inputs at V_{CC} or GND	Outputs disabled			0.05		0.05	mA
	Control inputs	V_{CC} = 5.5 V, One input at 3.4 V,	Other inputs at V_{CC} or GND	1.5				1.5	
Ci		V _I = 2.5 V or 0.5 V			3				pF
Co		$V_0 = 2.5 \text{ V or } 0.5 \text{ V}$			7				pF

[†] All typical values are at V_{CC} = 5 V.
[‡] Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

§ This limit may vary among suppliers.

[¶] This is the increase in supply current for each input that is at the specified TTL voltage level, rather than V_{CC} or GND.



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switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 1)

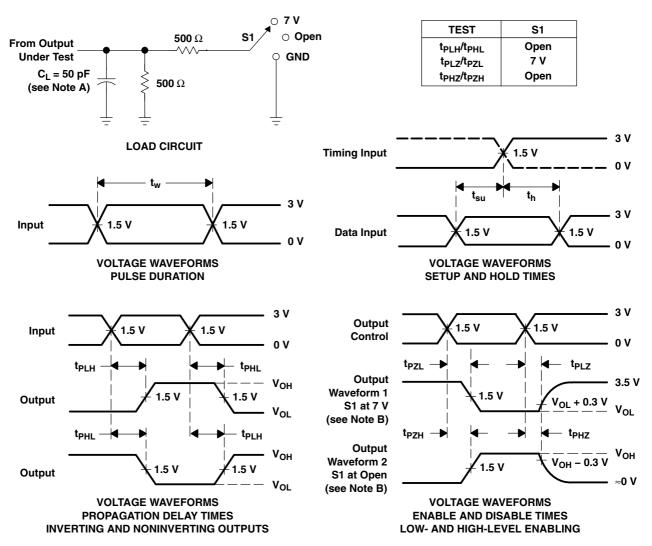
PARAMETER	FROM	TO	V ₀ T,	_{CC} = 5 V _A = 25°C	9	MIN	МАХ	UNIT
	(INPUT)	(OUTPUT)	MIN	TYP	MAX			
t _{PLH} †	•	V	1	3.2	4.6	1	6	
t _{PHL} †	A	Ŷ	1	2.5	4.6	1	6.2	6.2 ns
t _{PZH} †		V	1	3.6	5	1	6	
t _{PZL} †	ŌĒ	Y	1	2.5	6.2	1	7.5	ns
t _{PHZ}	A.F.	V	1	3.8	5.4	1	6.3	
t _{PLZ} †	ŌĒ	Ý	1	3.3	5.3	1	6.5	ns

[†] This limit may vary among suppliers.



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PARAMETER MEASUREMENT INFORMATION

NOTES: A. C₁ includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control. C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_Q = 50 Ω , t_r \leq 2.5 ns, t_f \leq 2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. All parameters and waveforms are not applicable to all devices.

Figure 1. Load Circuit and Voltage Waveforms





10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74ABT125QDRG4Q1	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	ABT125Q	Samples
SN74ABT125QDRQ1	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	ABT125Q	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <= 1000ppm threshold. Antimony trioxide based flame retardants must also meet the <= 1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

10-Dec-2020

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.



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